

OPA8740HP

High Speed

Infrared LED Chip

GaAlAs/GaAlAs

1. Material Substrate GaAlAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)

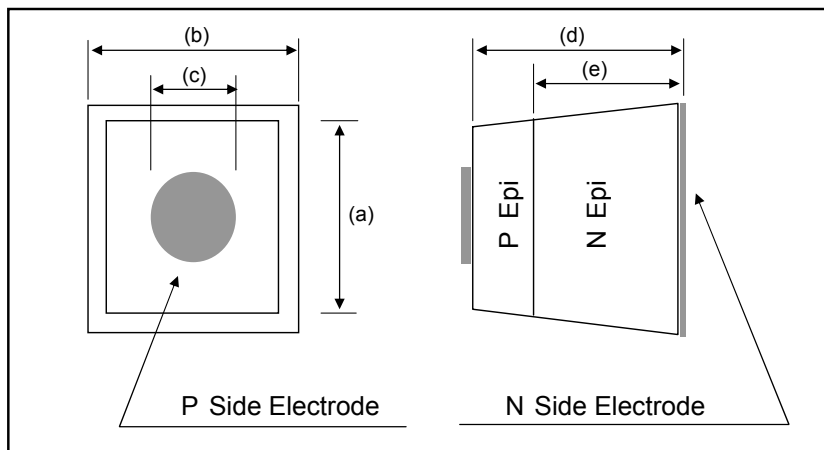
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$			2.2	V	IF=50mA
Reverse Voltage	V_R	4			V	IR=10uA
Power	P_O	10	15		mW	IF=50mA
Wavelength	λ_P		870		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		15		ns	
Fall Time	T_f		6.3		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data**
- (a) Emission Area ----- 14.7mil x 14.7mil
 - (b) Bottom Area ----- 15.7mil x 15.7mil
 - (c) Bonding Pad ----- 150um
 - (d) Chip Thickness ----- 7mil
 - (e) Junction Height ----- 6.4mil



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